

## Electronic Acknowledgement Receipt

<b>EFS ID:</b>	8353578
<b>Application Number:</b>	10565621
<b>International Application Number:</b>	
<b>Confirmation Number:</b>	2319
<b>Title of Invention:</b>	Stacked structure and production method thereof
<b>First Named Inventor/Applicant Name:</b>	Hubert Moriceau
<b>Customer Number:</b>	90678
<b>Filer:</b>	Jasper W. Dockrey
<b>Filer Authorized By:</b>	
<b>Attorney Docket Number:</b>	9905-37 (BIF116044/US)
<b>Receipt Date:</b>	03-SEP-2010
<b>Filing Date:</b>	25-JUL-2006
<b>Time Stamp:</b>	17:05:42
<b>Application Type:</b>	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
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### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/Message Digest	Multi Part/.zip	Pages (if appl.)
1	NPL Documents	15-NF-OA-10-05-05.pdf	283265 dd115ac98b430e605310eab577a3d0e27e-1dfe	no	8

### Warnings:

Information:
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2	NPL Documents	15-F-OA-05-03-06.pdf	400743 ZM5l0fHt051e02hd4693e9557dca3992 .pecc	no	11
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**Warnings:****Information:**

3	NPL Documents	15-NF-OA-01-10-07.pdf	457128 6095d25462cea744b4bd03d3e104a72c85 66dce	no	12
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4	NPL Documents	15-F-OA-07-20-07.pdf	448778 0e26ff443a30141d11abbaa1d4a4f5a2c2 5a11	no	12
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**Warnings:****Information:**

5	NPL Documents	15-NF-OA-02-11-08.pdf	407731 6f1c5a518a98bc3e4bb4a112cd4854e9cc 1cc3	no	11
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6	NPL Documents	15-F-OA-10-29-08.pdf	416204 232bd7587351e1334b20e7b7ed3aef5 903e94	no	11
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7	NPL Documents	15-NF-OA-6-25-09.pdf	273969 99994b025406c7cadb158cc5ed815a02b 546d4	no	8
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8	NPL Documents	16-OA-NF-9-24-04_1.PDF	271574 6c5e42d4970b5136f27aeb1bf7980c94d5 3af1e	no	7
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21	NPL Documents	34-OA-NF-11-27-09.pdf	352471 4ef7ccfebf476393c6c291ab15c2538 0eca	no	10
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23	NPL Documents	Ono_et_al_Orientation_Dependence_of_Flaking_of_Ion_Irradiated.pdf	349210 99628b4eff6a332091948bc73b43b372c79 45db	no	6
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24	NPL Documents	Paszti_E_Flaking_and_Wave-Like_Structure_On_Metallic_Glasses_Induced_By_MeV-Energy_Helium_Ions.pdf	811448 098056254d5e0fb3636212c91a605ef0f 081d	no	8
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25	NPL Documents	Picraux_S_Thomas_et_al_Ion_Implantation_of_Surfaces.pdf	623657 6601c279798d132a9e5a7a92a3a6241861 0ea	no	9
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26	NPL Documents	Pollentier_et_al-Fabrication_of_High-Radiance_LEDs_by_Epitaxial_Lift-Off.pdf	849591 a60b652406086a1630d248ed3ed7591495 17239d	no	7
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27	NPL Documents	Popov-VP-Blistering-On-A-Silicon-Surface_1.PDF	502658 8d475b117b5ac3237d258ecf4b93f5c771 0ea38	no	9
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28	NPL Documents	Primak_W-Impurity_Effect_In_the_Ionization_Dilation_of_Vitreous_Silica.pdf	792830 as280/eu73b57d614234fd2ea25ae26fe 4960f	no	8
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29	NPL Documents	Reissue_US_App_No_10-44978 6.pdf	669741 ebdbdeb722728753eab026e160c0f6bb5a/ 872bc0l	no	12
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30	NPL Documents	Renier_M_et_al_A_New_Low- energy_Ion_Implanter.pdf	82450 data:acfbfb137242f29a5c50d861d116e975c/ 8538	no	2
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32	NPL Documents	Sah_Chih-Tang_et_al- Deactivation_of_the_Boron_Ac- ceptor_in_Silicon_by_Hydroge- n.pdf	300754 43324ff1026228edc77ea/bd6efef024d966/ 1927	no	3
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37	NPL Documents	Snyman_HC_et_al- Transmission_Electron_Microsc- opy_of_Extended_Crystal_Def- ects_in_Proton.pdf	4122704 8f14de2ee12a7f2d08027b66cd0f9e2/ 610e	no	32
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38	NPL Documents	Snyman,_HC_et_al-Void_Formation_in_Annealed_Proton-Bombarded_GaAs.pdf	291943 5e181d8fe3e464040fb566ex_9998aa 0ca4b	no	3
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39	NPL Documents	Stein,_H_et_al-Infrared_Spectroscopy_of_Chemically.pdf	579683 3faa7d513776eadd8f99467312401shz ab371	no	10
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40	NPL Documents	Stephan,_D_Invitation_of_Lattice_Strain_in_Proton-Irradiated.pdf	358634 612ed464feff5fb1c175e641123dc14c28f71 57c3	no	8
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41	NPL Documents	Sunkara,_et_al_Bulk_synthesis_of_silicon_nanowires_using_a_low-temperature_vapor-liquid.pdf	255212 a1026fb21198a4fb7b1dc8148fbfb9f75 b5685	no	3
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42	NPL Documents	Suzuki,_et_al-High_Speed_and_Low_Power_n-p_Double-Gate_SOI_CMOS.pdf	812023 a1046ec621664c4b8978b93cf800390c d1c5d	no	9
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43	NPL Documents	Sze,_SM_VLSI_Technology.pdf	107666 7689b7c9725e0473e578e6bd51126f 9c518	no	4
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44	NPL Documents	Tan,_TY_et_al-On_Oxygen_Precipitation_Retardation_Recovery_Phenoemna.pdf	563168 45522ebfb76476f23e7d401955705cc 219fb	no	11
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45	NPL Documents	Terada,_K_et_al-A_New_DRAM_Cell_With_A_Transistor_On_A_Lateral.pdf	446632 9098abc1114ab96e448f17af45194916520 4fd4fb	no	6
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46	NPL Documents	Terreault,_B-Hydrogen_Blistering_of_Silicon.pdf	337275 43d0es/ec0fb4410b9160bd77e2247fd 3659	no	4
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53	NPL Documents	Van_de_Walle_C_et_al-Theory_of_Hydrogen-Vol-60.pdf	285435 e3d755933463ad752a8b1463c5d97bcac0 05575	no	3
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54	NPL Documents	Van_de_Walle_C-Theoretical_Aspects_of_Hydrogen_in_Crystalline_Semiconductors.pdf	746426 93ee18001d20e4e03d45ac2419467b6a1 19be4	no	12
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55	NPL Documents	Van_de_Walle_C_et_al-Theory_of_Hydrogen_Diffusion_and_Reactions_In_Crystalline_Silicon.pdf	1957808 115D3be7a908c986c4756f71c117d910f 8c3	no	23
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<b>Information:</b>					
<b>Total Files Size (in bytes):</b> 35385648					
<p>This Acknowledgement Receipt evidences receipt on the noted date by the USPTO of the indicated documents, characterized by the applicant, and including page counts, where applicable. It serves as evidence of receipt similar to a Post Card, as described in MPEP 503.</p> <p><b>New Applications Under 35 U.S.C. 111.</b>  If a new application is being filed and the application includes the necessary components for a filing date (see 37 CFR 1.53(b)-(d) and MPEP 506), a Filing Receipt (37 CFR 1.54) will be issued in due course and the date shown on this Acknowledgement Receipt will establish the filing date of the application.</p> <p><b>National Stage of an International Application under 35 U.S.C. 371.</b>  If a timely submission to enter the national stage of an international application is compliant with the conditions of 35 U.S.C. 371 and other applicable requirements a Form PCT/DO/EO/903 indicating acceptance of the application as a national stage submission under 35 U.S.C. 371 will be issued in addition to the Filing Receipt, in due course.</p> <p><b>New International Application Filed with the USPTO as a Receiving Office</b>  If a new international application is being filed and the international application includes the necessary components for an international filing date (see PCT Article 11 and MPEP 1810), a Notification of the International Application Number and of the International Filing Date (Form PCT/RO/105) will be issued in due course, subject to prescriptions concerning national security, and the date shown on this Acknowledgement Receipt will establish the international filing date of the application.</p>					